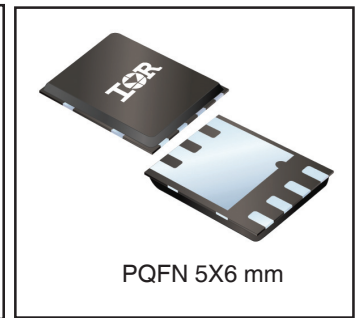
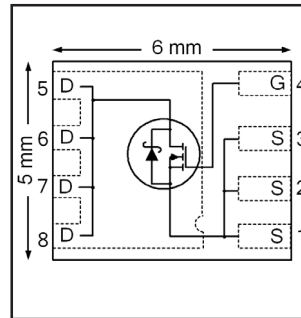


HEXFET® Power MOSFET

V_{DS}	30	V
$R_{DS(on) max}$ (@ $V_{GS} = 10V$)	2.5	mΩ
$V_{SD max}$ (@ $I_S = 5.0A$)	0.65	V
t_{rr} (typical)	19	ns
I_D (@ $T_{c(Bottom)} = 25°C$)	100 Ⓞ	A



Applications

- Synchronous MOSFET for high frequency buck converters

Features and Benefits

Features

Low $R_{DS(on)}$ (<2.5mΩ)
Schottky Intrinsic Diode with Low Forward Voltage
Low Thermal Resistance to PCB (<1.2°C/W)
100% Rg tested
Low Profile (<0.9 mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Industrial Qualification

results in
⇒

Benefits

Lower Conduction Losses
Lower Switching Losses
Increased Power Density
Increased Reliability
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRFH5302DTRPBF	PQFN 5mm x 6mm	Tape and Reel	4000	
IRFH5302DTR2PBF	PQFN-5mm-x-6mm	Tape and Reel	400	EOL Notice #259

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	
$I_D @ T_A = 25°C$	Continuous Drain Current, $V_{GS} @ 10V$	29	A
$I_D @ T_A = 70°C$	Continuous Drain Current, $V_{GS} @ 10V$	23	
$I_D @ T_{C(Bottom)} = 25°C$	Continuous Drain Current, $V_{GS} @ 10V$ Ⓞ	100	
$I_D @ T_{C(Bottom)} = 100°C$	Continuous Drain Current, $V_{GS} @ 10V$ Ⓞ	100	
I_{DM}	Pulsed Drain Current ①	400	
$P_D @ T_A = 25°C$	Power Dissipation ⑤	3.6	W
$P_D @ T_{C(Bottom)} = 25°C$	Power Dissipation ⑤	104	
	Linear Derating Factor ⑤	0.83	W/°C
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		

Notes ① through ⑥ are on page 8

Static @ T_J = 25°C (unless otherwise specified)

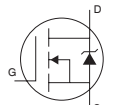
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 500μA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	-0.25	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	2.0	2.5	mΩ	V _{GS} = 10V, I _D = 50A ③
		—	3.1	3.7		V _{GS} = 4.5V, I _D = 50A ③
V _{GS(th)}	Gate Threshold Voltage	1.35	1.80	2.35	V	V _{DS} = V _{GS} , I _D = 100μA
ΔV _{GS(th)}	Gate Threshold Voltage Coefficient	—	-10	—	mV/°C	
I _{DSS}	Drain-to-Source Leakage Current	—	—	500	μA	V _{DS} = 24V, V _{GS} = 0V
		—	—	5.0	mA	V _{DS} = 24V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
g _{fs}	Forward Transconductance	110	—	—	S	V _{DS} = 15V, I _D = 50A
Q _g	Total Gate Charge	—	55	—	nC	V _{GS} = 10V, V _{DS} = 15V, I _D = 50A
Q _g	Total Gate Charge	—	26	39	nC	V _{DS} = 15V V _{GS} = 4.5V I _D = 50A
Q _{gs1}	Pre-V _{th} Gate-to-Source Charge	—	6.2	—		
Q _{gs2}	Post-V _{th} Gate-to-Source Charge	—	4.0	—		
Q _{gd}	Gate-to-Drain Charge	—	7.9	—		
Q _{godr}	Gate Charge Overdrive	—	7.9	—		
Q _{sw}	Switch Charge (Q _{gs2} + Q _{gd})	—	11.9	—		
Q _{oss}	Output Charge	—	19	—	nC	V _{DS} = 16V, V _{GS} = 0V
R _G	Gate Resistance	—	1.9	—	Ω	
t _{d(on)}	Turn-On Delay Time	—	16	—	ns	V _{DD} = 15V, V _{GS} = 4.5V I _D = 50A R _G = 1.8Ω
t _r	Rise Time	—	30	—		
t _{d(off)}	Turn-Off Delay Time	—	20	—		
t _f	Fall Time	—	12	—		
C _{iss}	Input Capacitance	—	3635	—	pF	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz
C _{oss}	Output Capacitance	—	680	—		
C _{rss}	Reverse Transfer Capacitance	—	260	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy ②	—	130	mJ
I _{AR}	Avalanche Current ①	—	50	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	100	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	400		
V _{SD}	Diode Forward Voltage	—	—	0.65	V	T _J = 25°C, I _S = 5.0A, V _{GS} = 0V ③
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _J = 25°C, I _S = 50A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	19	29	ns	T _J = 25°C, I _F = 50A, V _{DD} = 15V
Q _{rr}	Reverse Recovery Charge	—	28	42	nC	di/dt = 300A/μs ③
t _{on}	Forward Turn-On Time	Time is dominated by parasitic Inductance				


Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC} (Bottom)	Junction-to-Case ④	—	1.2	°C/W
R _{θJC} (Top)	Junction-to-Case ④	—	15	
R _{θJA}	Junction-to-Ambient ⑤	—	35	
R _{θJA} (<10s)	Junction-to-Ambient ⑤	—	22	

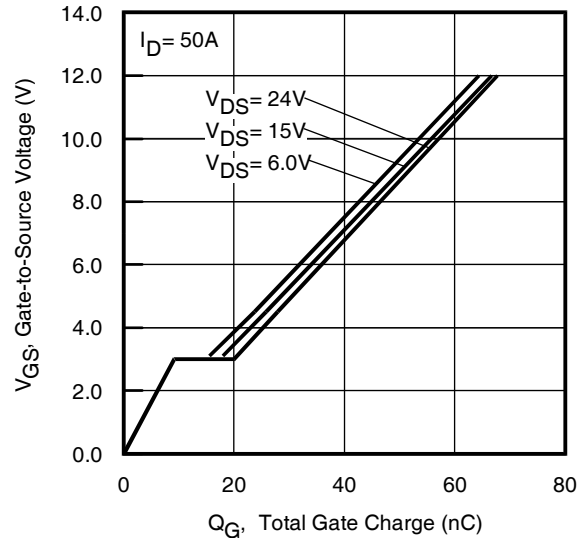
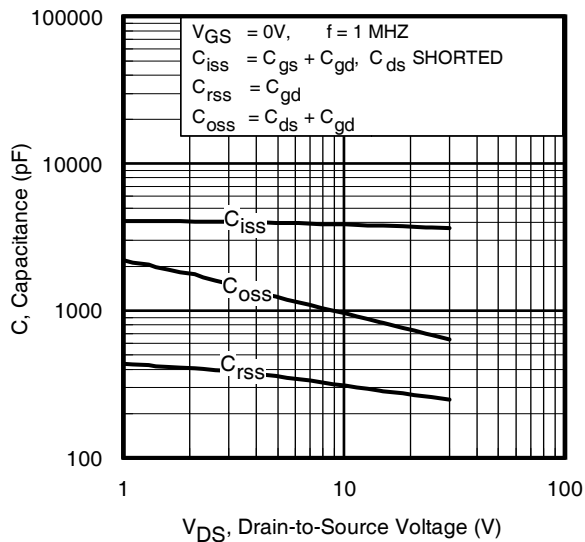
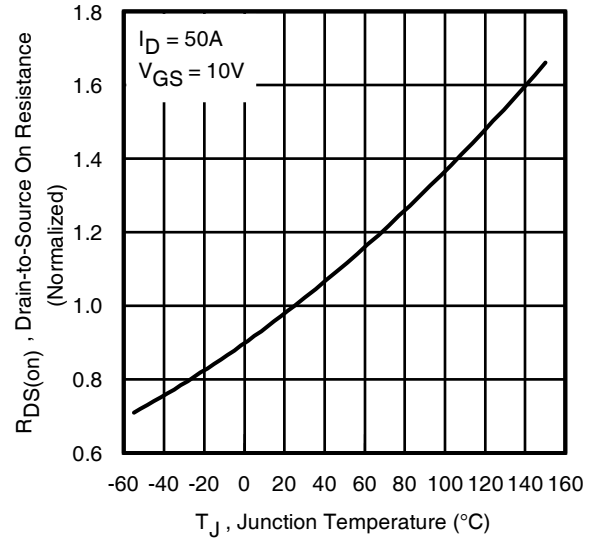
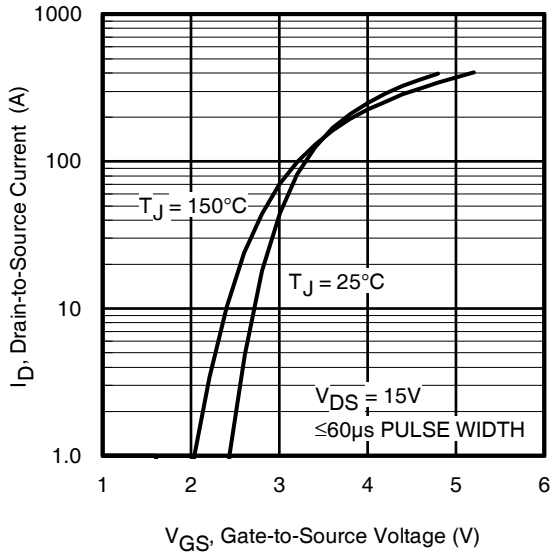
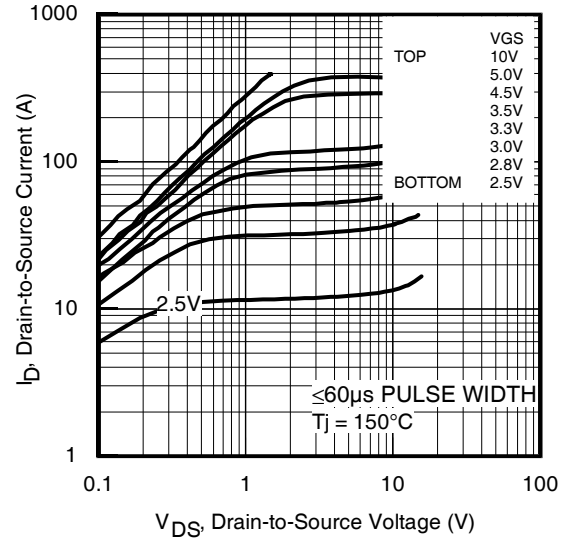
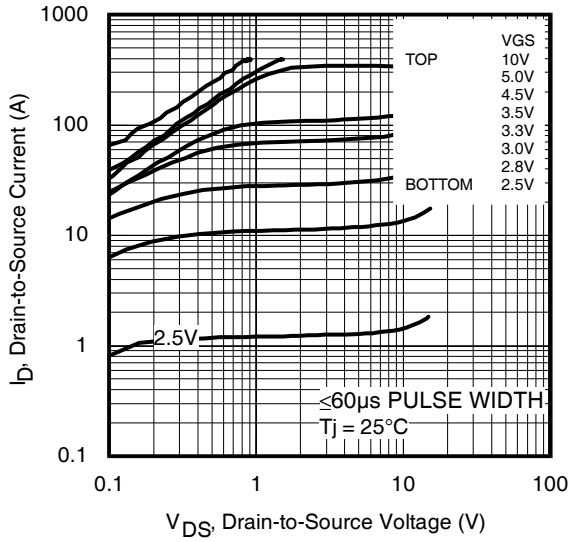
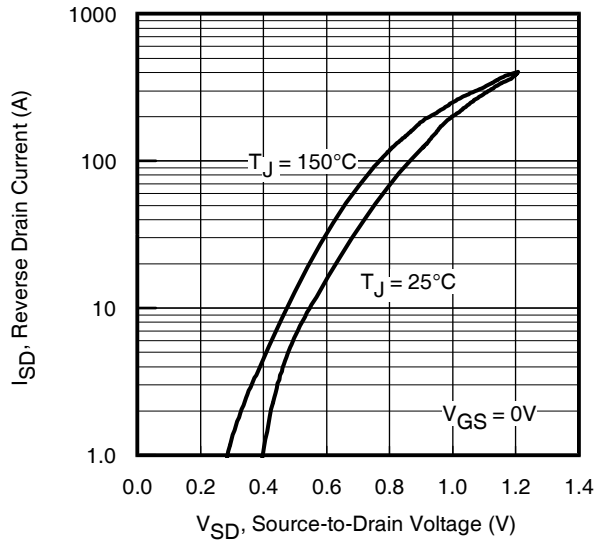
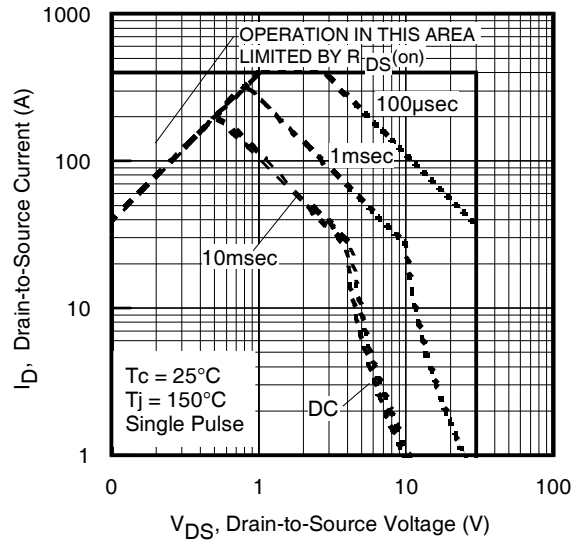
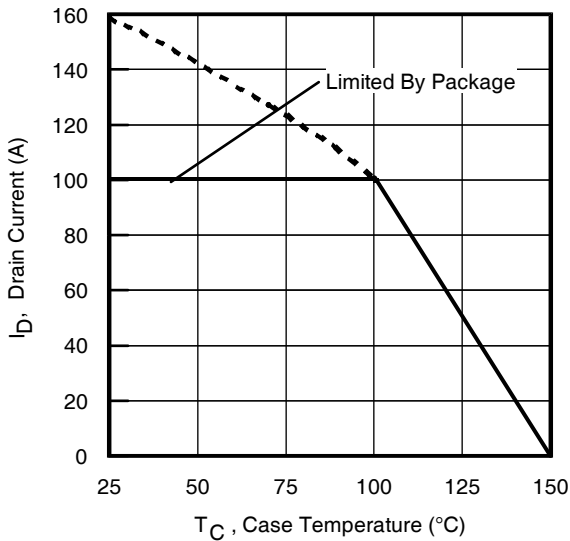
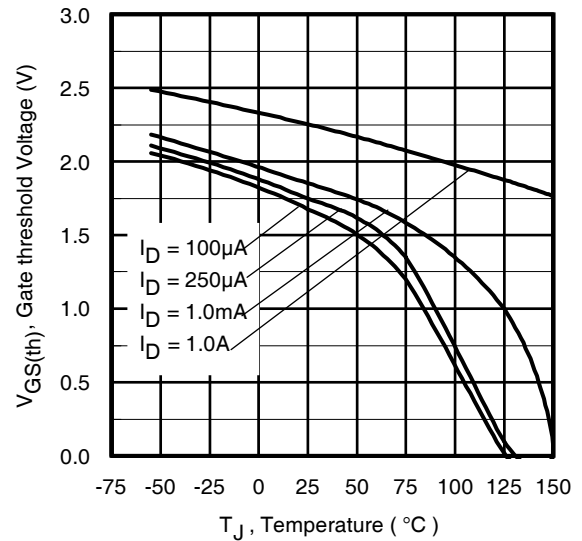
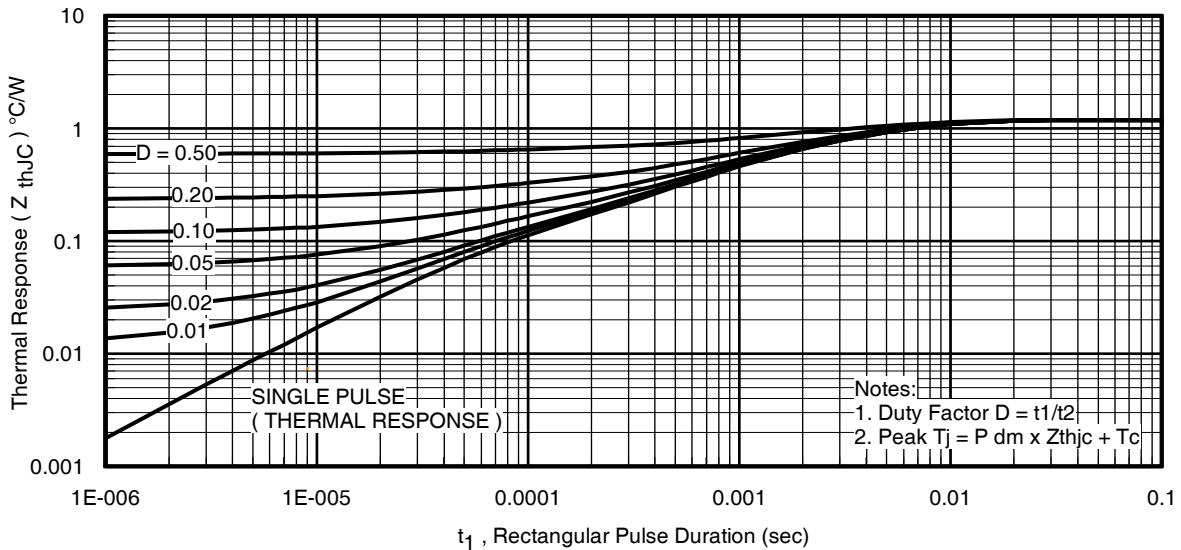
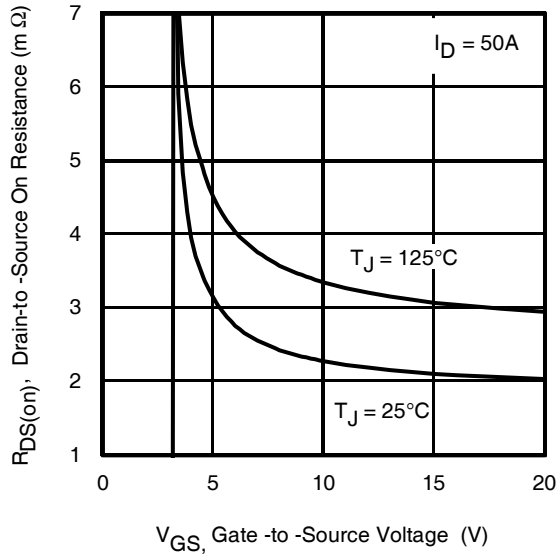
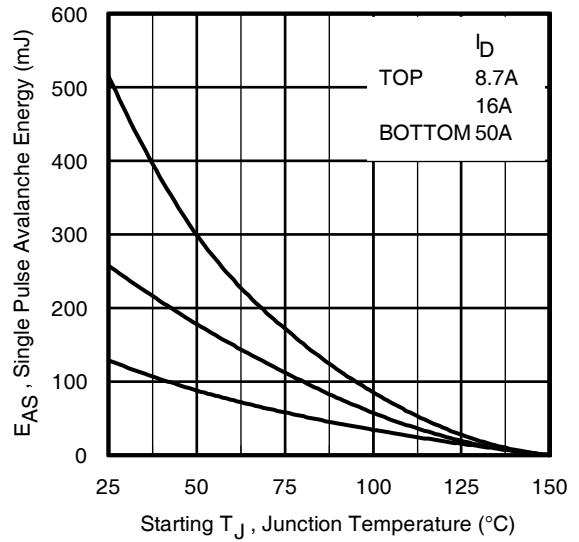
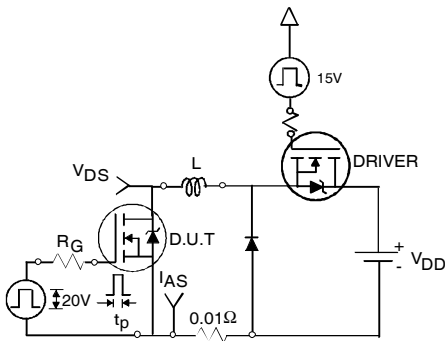
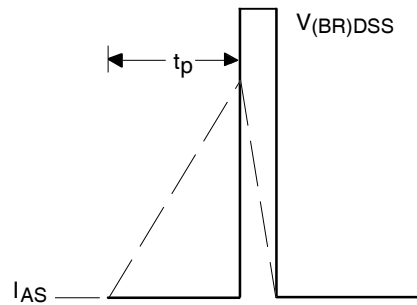
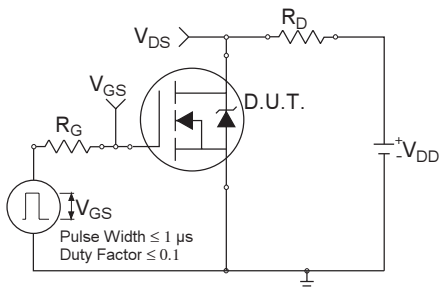
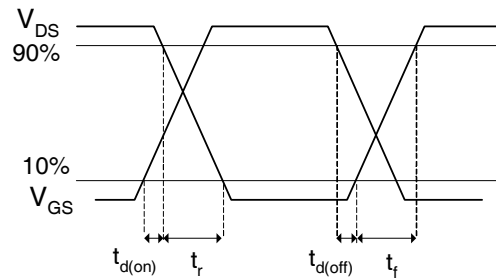


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage


Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig 9. Maximum Drain Current vs. Case (Bottom) Temperature

Fig 10. Threshold Voltage vs. Temperature

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case (Bottom)


Fig 12. On-Resistance vs. Gate Voltage

Fig 13. Maximum Avalanche Energy vs. Drain Current

Fig 14a. Unclamped Inductive Test Circuit

Fig 14b. Unclamped Inductive Waveforms

Fig 15a. Switching Time Test Circuit

Fig 15b. Switching Time Waveforms

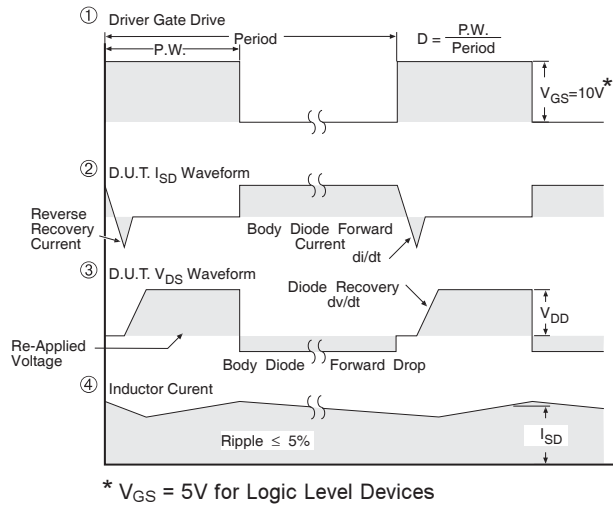
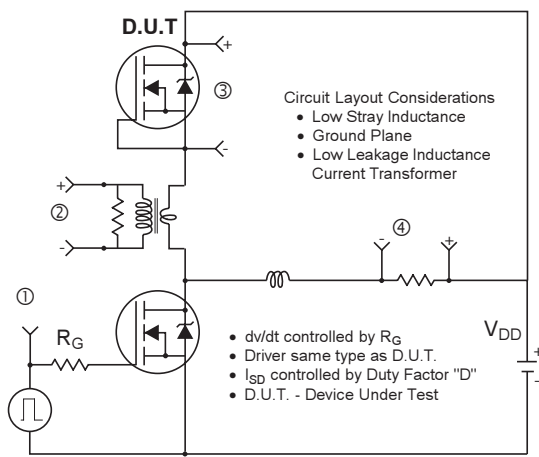


Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET[®] Power MOSFETs

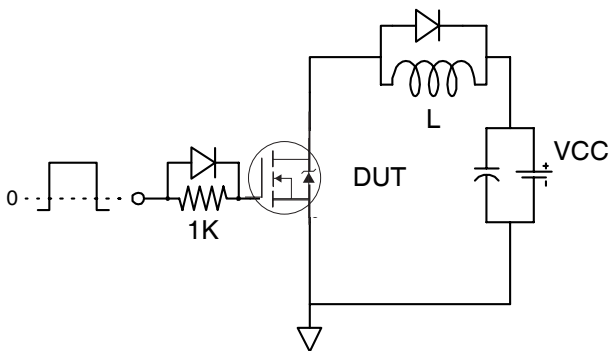


Fig 17. Gate Charge Test Circuit

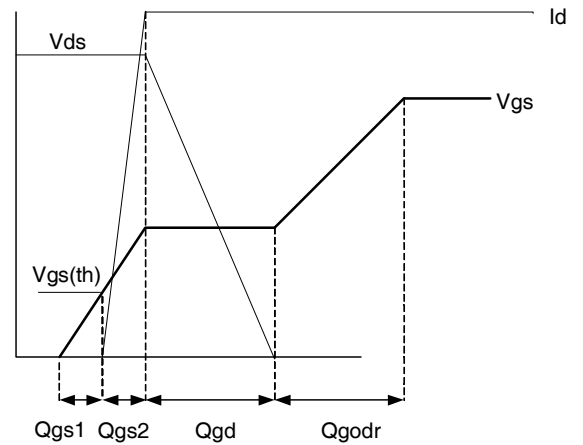
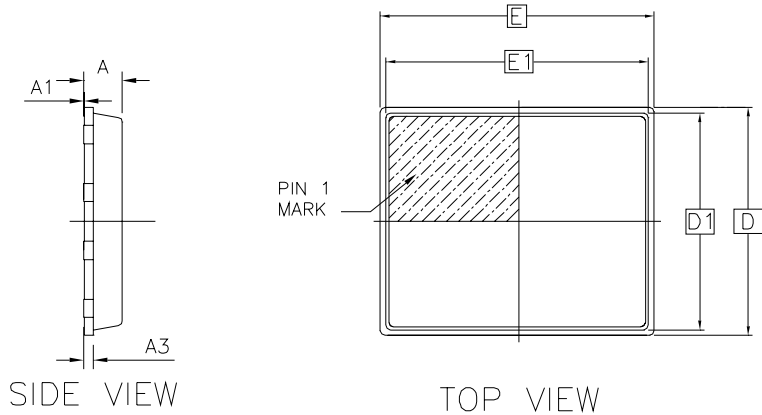
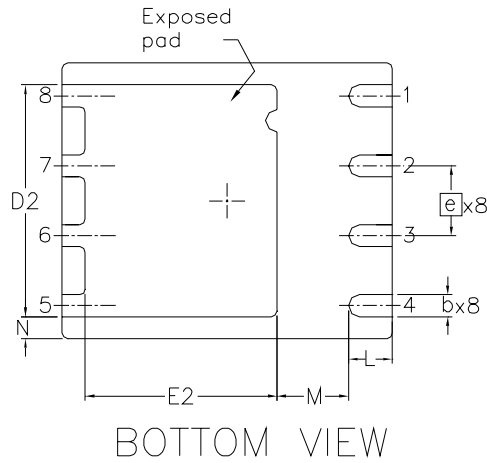


Fig 18. Gate Charge Waveform

PQFN 5x6 Outline "B" Package Details



OUTLINE PQFN 5x6B				
DIM SYMBOL	MIN	NOM	MAX	
A	0.80	0.83	0.90	
A1	0	0.020	0.05	
A3		0.20		REF
b	0.35	0.40	0.47	
D		5.00		BSC
D1		4.75		BSC
D2	4.10	4.21	4.30	
e		1.27		BSC
E		6.00		BSC
E1		5.75		BSC
E2	3.38	3.48	3.58	
L	0.70	0.80	0.90	
M		1.30		REF
N		0.40		REF



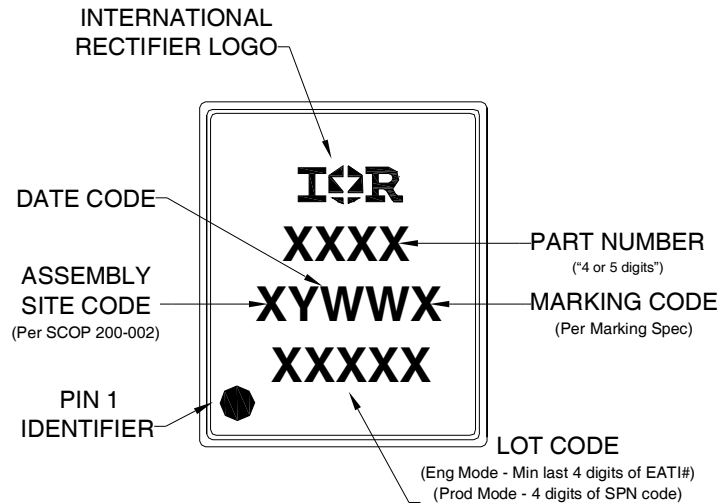
For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136:

<http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154:

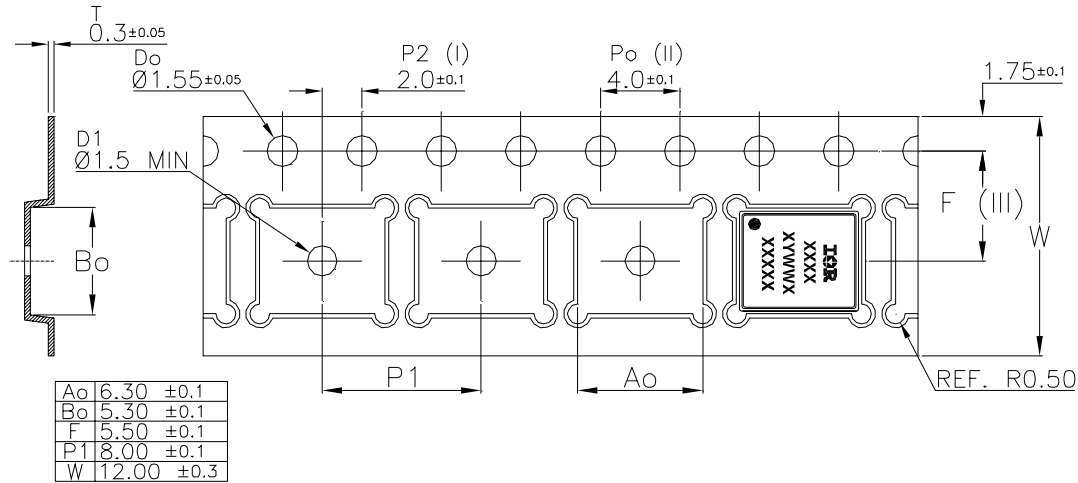
<http://www.irf.com/technical-info/appnotes/an-1154.pdf>

PQFN 5x6 Outline "B" Part Marking



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

PQFN 5x6 Outline "B" Tape and Reel



Qualification information[†]

Qualification level	Industrial ^{††} (per JEDEC JESD47F ^{†††} guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-ST D-020D ^{†††})
RoHS compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site

<http://www.irf.com/product-info/reliability>

^{††} Higher qualification ratings may be available should the user have such requirements.

Please contact your International Rectifier sales representative for further information:

<http://www.irf.com/whoto-call/salesrep/>

^{†††} Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.14\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 50\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_{θ} is measured at T_J of approximately 90°C .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package is limited to 100A by production test capability.

Revision History

Date	Comment
3/31/2010	• Idss limits at $T_J 25^\circ\text{C}$ is changed to $500\mu\text{A}$ max, $V_{ds} = 24\text{V}$ and at $T_J 125^\circ\text{C}$ it is changed to 5.0mA max, $V_{ds} = 24\text{V}$. All other parameters remain unchanged.
1/6/2014	• Updated ordering information to reflect the End-Of-Life (EOL) of the mini-reel option (EOL notice #259). • Updated data sheet with the new IR corporate template.